

THYRISTOR MODULE

PK(PD,PE,KK)130F

TOP



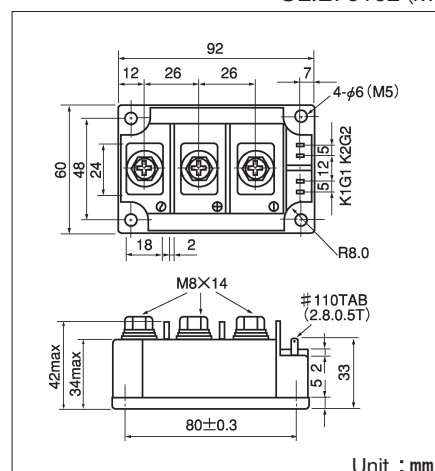
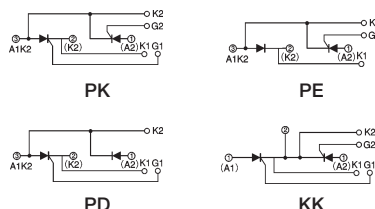
UL:E76102 (M)

Power Thyristor/Diode Module **PK130F** series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 1,600V are available. Two elements in a package and electrically isolated mounting base make your mechanical design easy.

- $I_{T(AV)}$ 130A, $I_{T(RMS)}$ 205A, I_{TSM} 4400A
- di/dt 200 A/ μ s
- dv/dt 500V/ μ s

(Applications)

Various rectifiers
AC/DC motor drives
Heater controls
Light dimmers
Static switches



Maximum Ratings

Symbol	Item	Ratings				Unit
		PK130F40 PD130F40 PE130F40 KK130F40	PK130F80 PD130F80 PE130F80 KK130F80	PK130F120 PD130F120 PE130F120 KK130F120	PK130F160 PD130F160 PE130F160 KK130F160	
VRRM	* Repetitive Peak Reverse Voltage	400	800	1200	1600	V
VRSM	* Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V
VDRM	Repetitive Peak Off-State Voltage	400	800	1200	1600	V

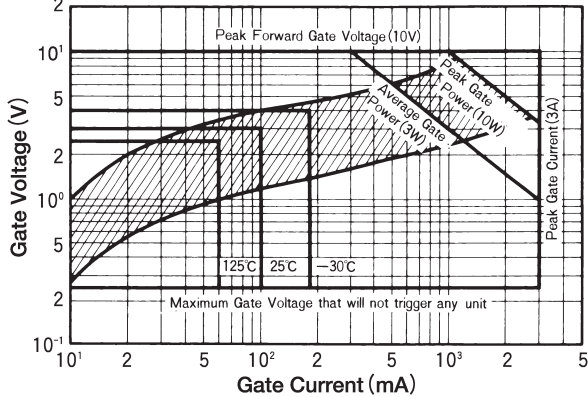
Symbol	Item		Conditions	Ratings	Unit
IT (AV)	*Average On-State Current		Single phase, half wave, 180° conduction, Tc : 90℃	130	A
IT (RMS)	*R.M.S. On-State Current		Single phase, half wave, 180° conduction, Tc : 90℃	205	A
ITSM	*Surge On-State Current		1/2cycle, 50Hz/60Hz, peak Value, non-repetitive	4000/4400	A
I²t	*I²t		Value for one cycle of surge current	8×10⁴	A²S
PGM	Peak Gate Power Dissipation			10	W
PG (AV)	Average Gate Power Dissipation			3	W
IFGM	Peak Gate Current			3	A
VFGM	Peak Gate Voltage (Forward)			10	V
VRGM	Peak Gate Voltage (Reverse)			5	V
di／dt	Critical Rate of Rise of On-State Current		IG=100mA, Tj=25℃, VD=1/2VDRM, dIG/dt=0.1A／μs	200	A／μs
VISO	*Isolation Breakdown Voltage (R.M.S.)		A.C.1minute	2500	V
Tj	*Operating Junction Temperature			－40～＋125	℃
Tstg	*Storage Temperature			－40～＋125	℃
	Mounting Torque	Mounting (M5)	Recommended 1.5～2.5 (15～25)	2.7 (28)	N・m (kgf・cm)
		Terminal (M8)	Recommended 8.8～10 (90～105)	11 (115)	
	Mass			510	g

Electrical Characteristics

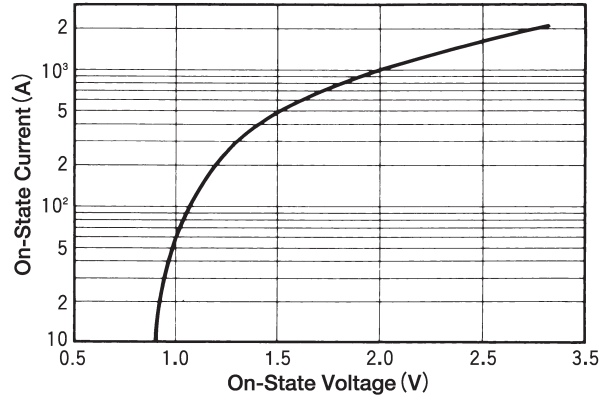
Symbol	Item	Conditions	Ratings	Unit
I _{DRM}	Repetitive Peak Off-State Current, max.	at V _{DRM} , single phase, half wave, $T_j = 125^\circ\text{C}$	50	mA
I _{RRM}	* Repetitive Peak Reverse Current, max.	at V _{DRM} , single phase, half wave, $T_j = 125^\circ\text{C}$	50	mA
V _{TM}	* Peak On-State Voltage, max.	On-State Current 400A, $T_j = 25^\circ\text{C}$ Inst. measurement	1.40	V
I _{GT} /V _{GT}	Gate Trigger Current/Voltage, max.	$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	100/3	mA/V
V _{GD}	Non-Trigger Gate, Voltage. min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{1}{2}V_{DRM}$	0.25	V
t _{gt}	Turn On Time, max.	$I_T = 130\text{A}$, $I_G = 100\text{mA}$, $T_j = 25^\circ\text{C}$, $V_D = \frac{1}{2}V_{DRM}$, $di_G/dt = 0.1\text{A}/\mu\text{s}$	10	μ s
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{2}{3}V_{DRM}$, Exponential wave.	500	V/ μ s
I _H	Holding Current, typ.	$T_j = 25^\circ\text{C}$	50	mA
I _L	Latching Current, typ.	$T_j = 25^\circ\text{C}$	100	mA
R _{th(j-c)}	* Thermal Impedance, max.	Junction to case	0.2	°C/W

* mark : Thyristor and Diode part. No mark : Thyristor part

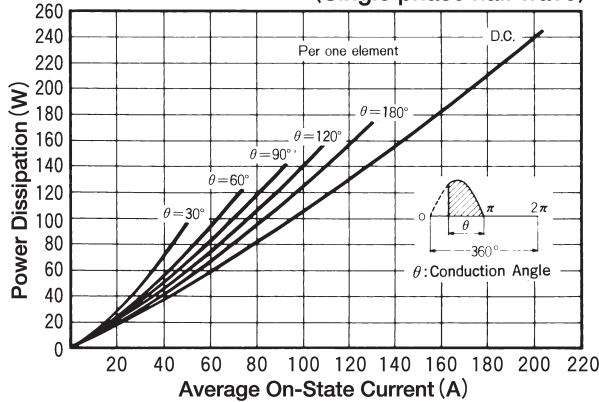
Gate Characteristics



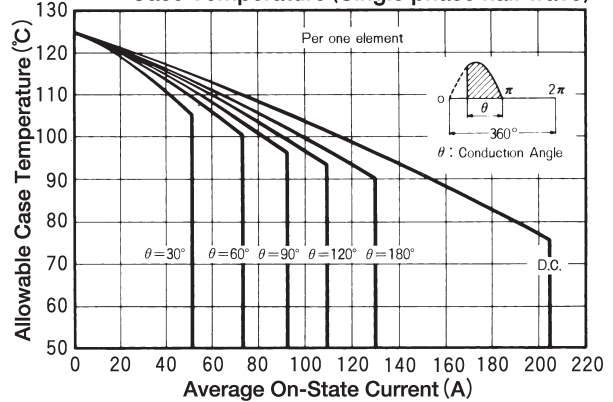
On-State Voltage max



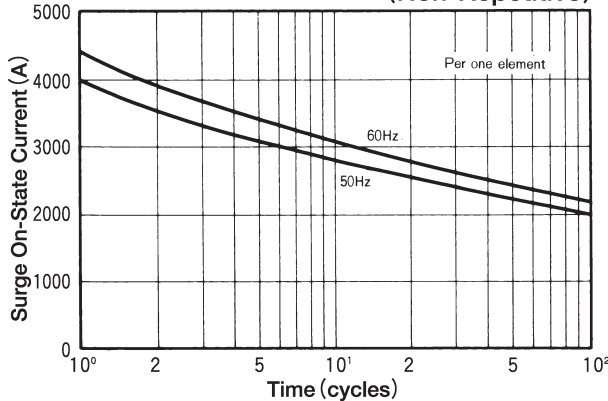
Average On-State Current Vs Power Dissipation (Single phase half wave)



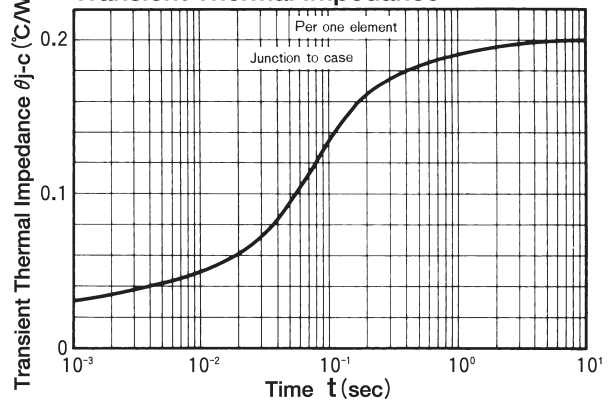
Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



Surge On-State Current Rating (Non-Repetitive)

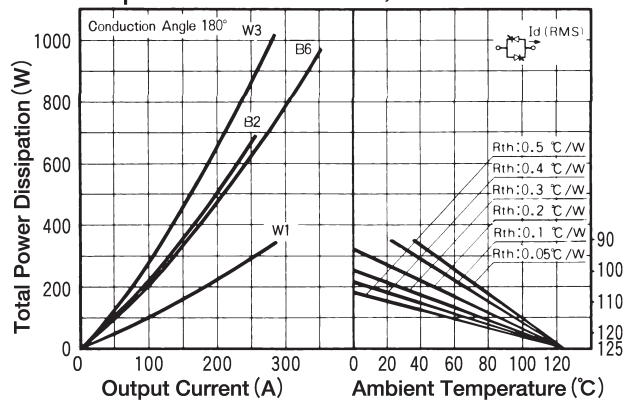


Transient Thermal Impedance

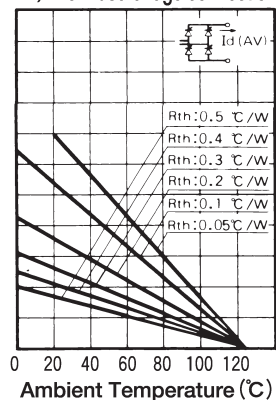


Output Current

W1; Bidirectional connection



B2; Two Pluse bridge connection



B6; Six pulse bridge connection

W3; Three phase bidirectional connection

